

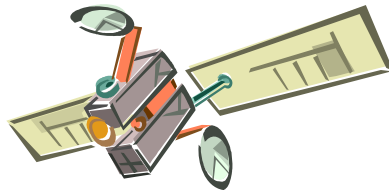
Electronics



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Bottom-up approach
self-assembly of
nanoscale object via
self-organisation.

Top-down approach
making micro- and
nanometre-scale
devices by growing
layered materials and
patterning bulk
materials.

New regimes for electronic
properties of material with
reduced dimensions,
due to the quantum effects in
the electronic system.

Nano- and micro-electronic systems / devices

Top-down manufacturing methods: growth and lithography.

Use of AFM for nanoprocessing.

Lithographically defined one-dimensional wires in
semiconductors.

Electronics =

electronic transport + sensitivity of transport characteristics to external conditions:

magnetic field,
temperature,
electromagnetic environment.

Electronics materials:

Semiconductors and semiconductor heterostructures
Normal and Ferromagnetic metals, Superconductor

Electron dynamics in each material is determined by

METALS — E_F

band structure ~1eV

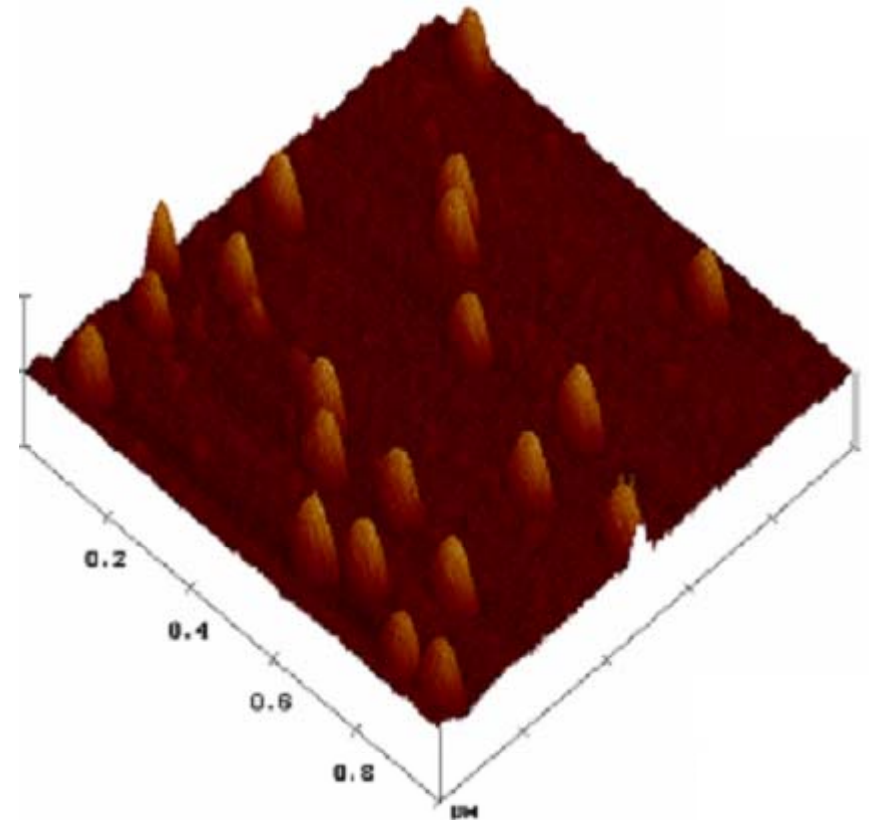
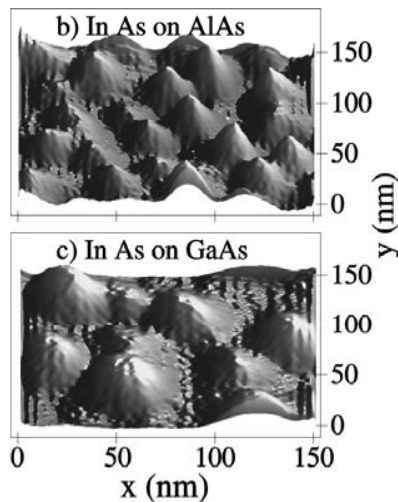
semicond. structures
SEMICONDUCTORS — E_F

correlations <1meV

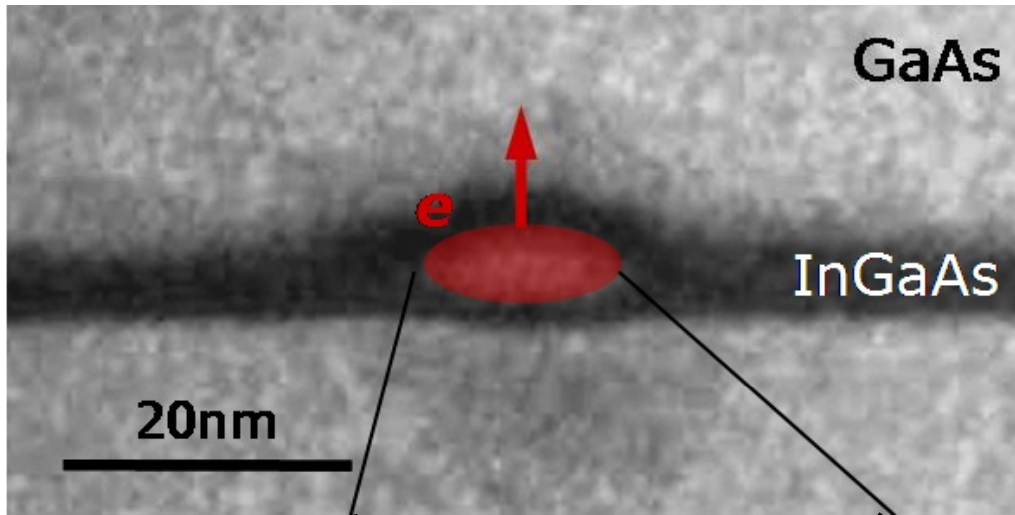
INSULATORS — E_F

Self-assembled semiconductor dots

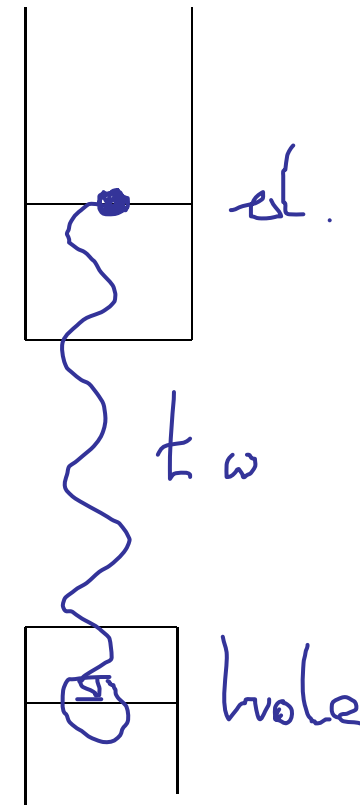
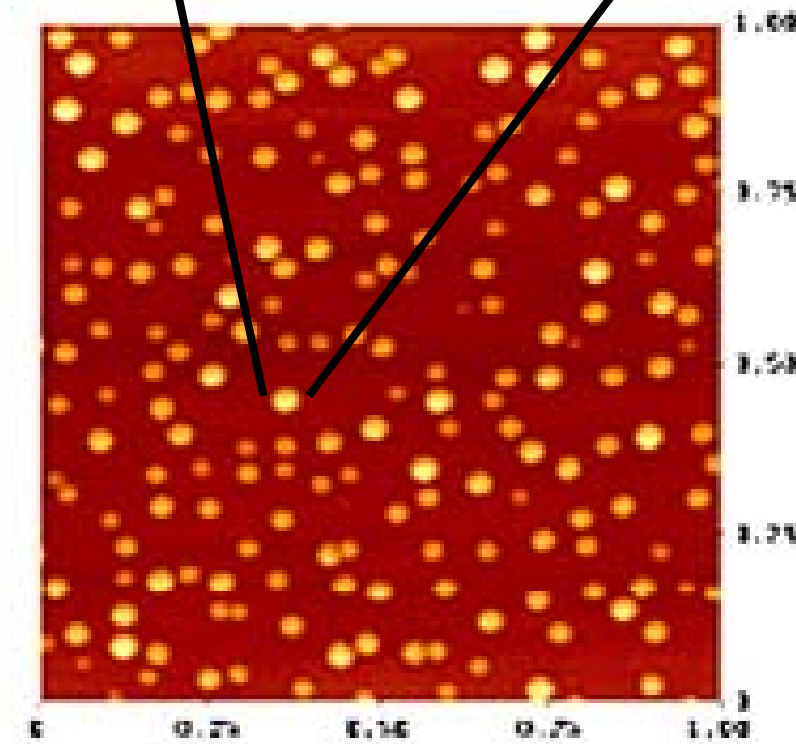
Due to lattice mismatch between two semiconductor materials, dots of one material tend to form, by themselves, on the surface of another: 'self-organisation'.



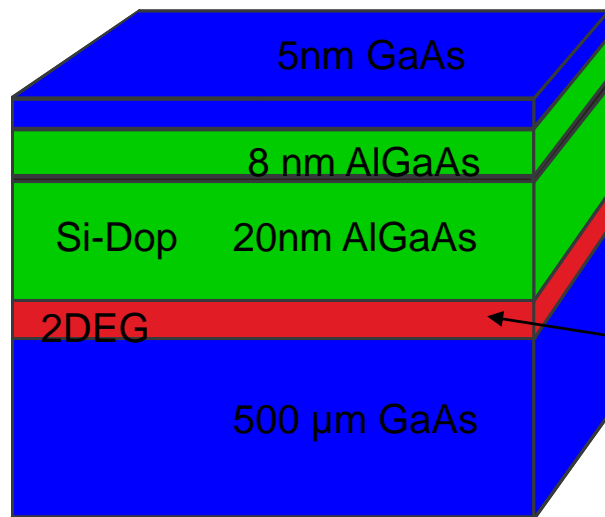
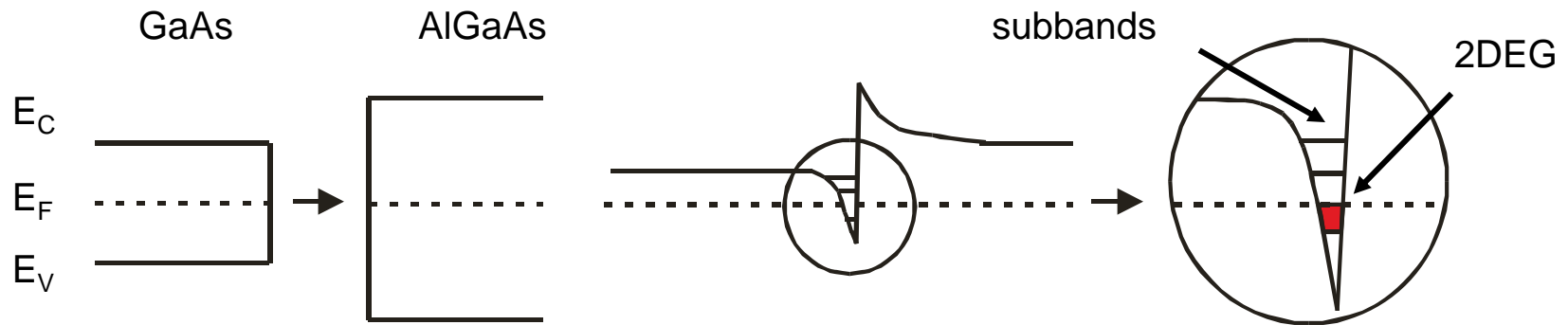
InP dots formed on the GaInP surface (AFM scan)



TEM image of an InGaAs/GaAs dot



Semiconductor Heterostructures



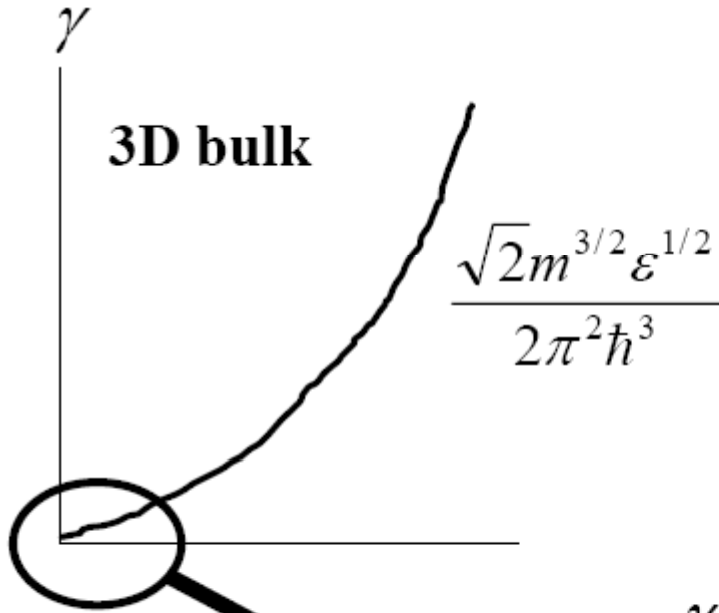
**made by MBE:
molecular beam epitaxy**

**band-edge discontinuity produces
a triangular well → 2DEG**

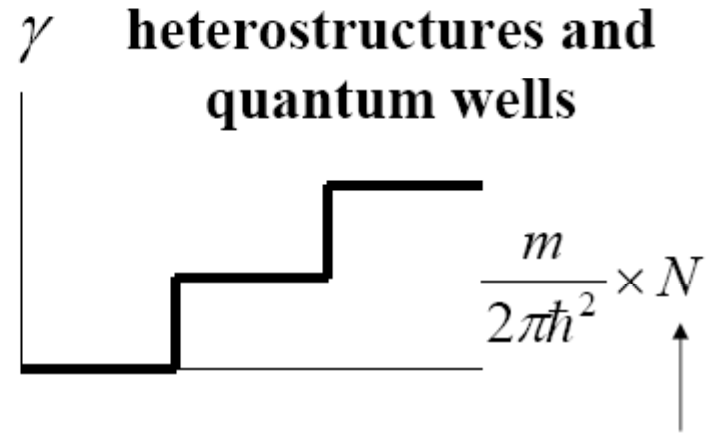
2DEG is a metal with a very low density

$$n_{2DEG} \sim 10^{10} - 10^{12} \text{ cm}^{-2}$$

Density of states, γ



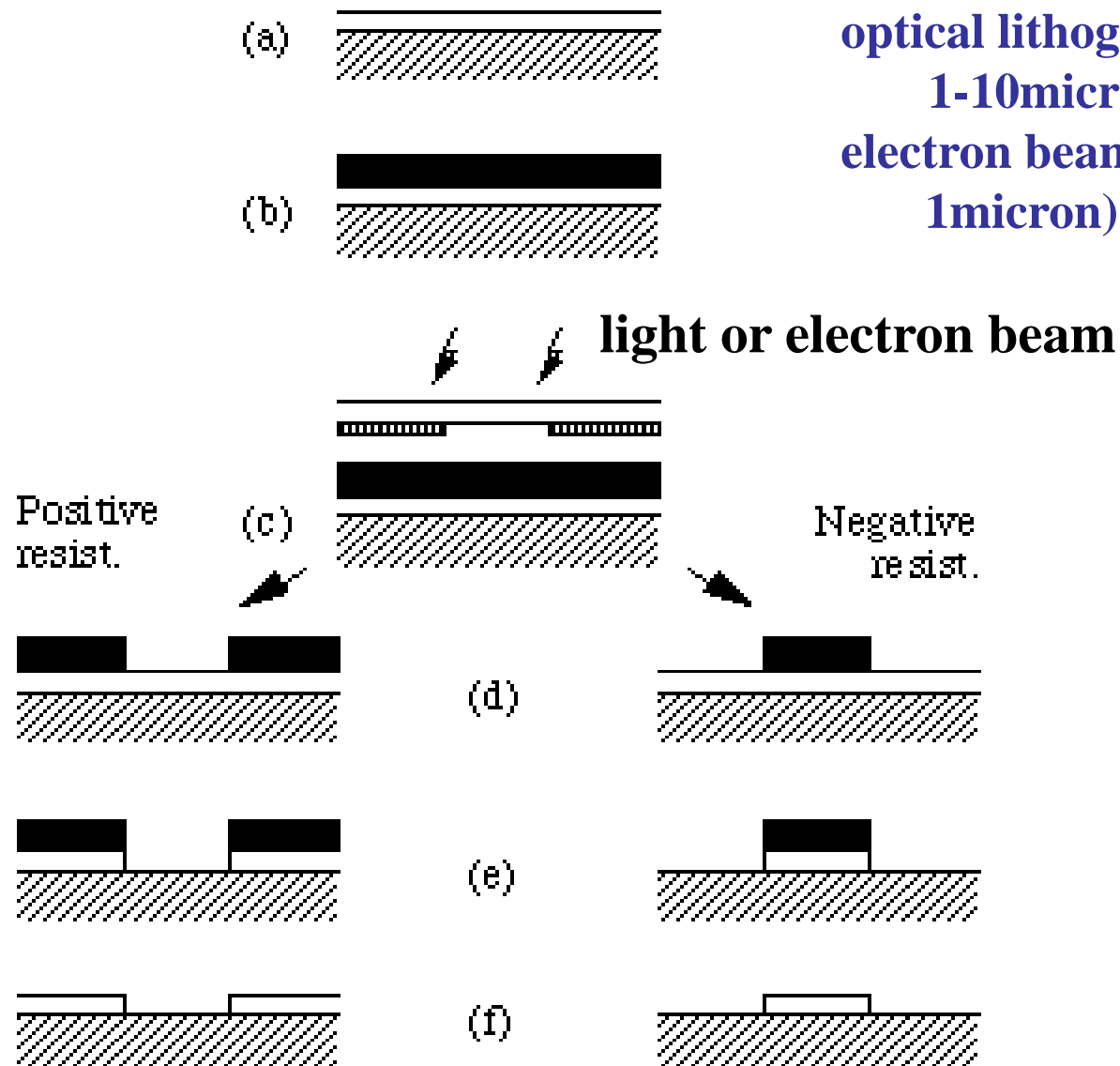
Electrons in heterostructures and quantum wells



Number of occupied subbands

↑

How to make micro/nanostructures: wires and dots

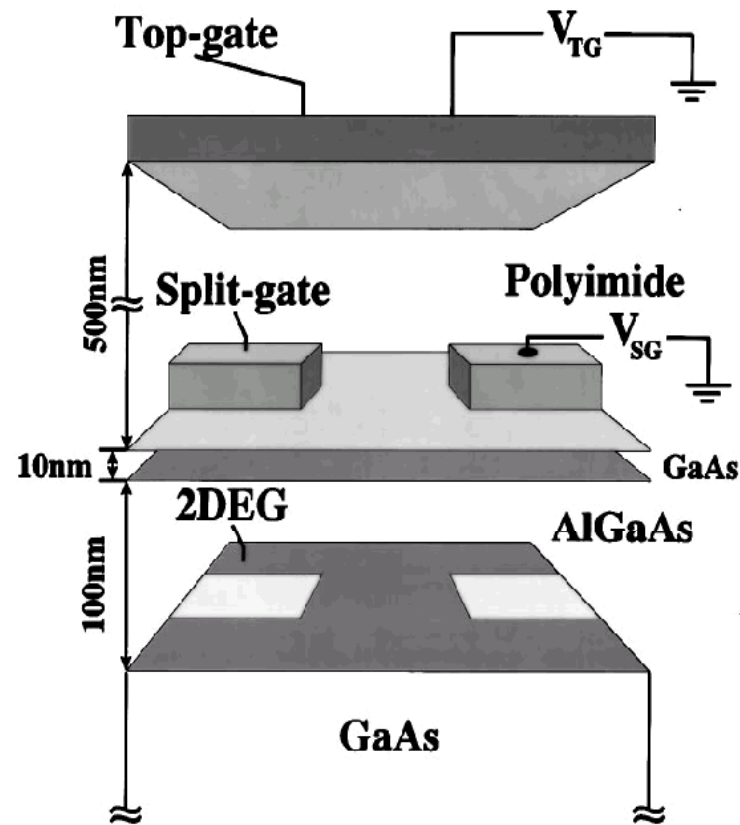


optical lithography (visible/UV light,
1-10microns)

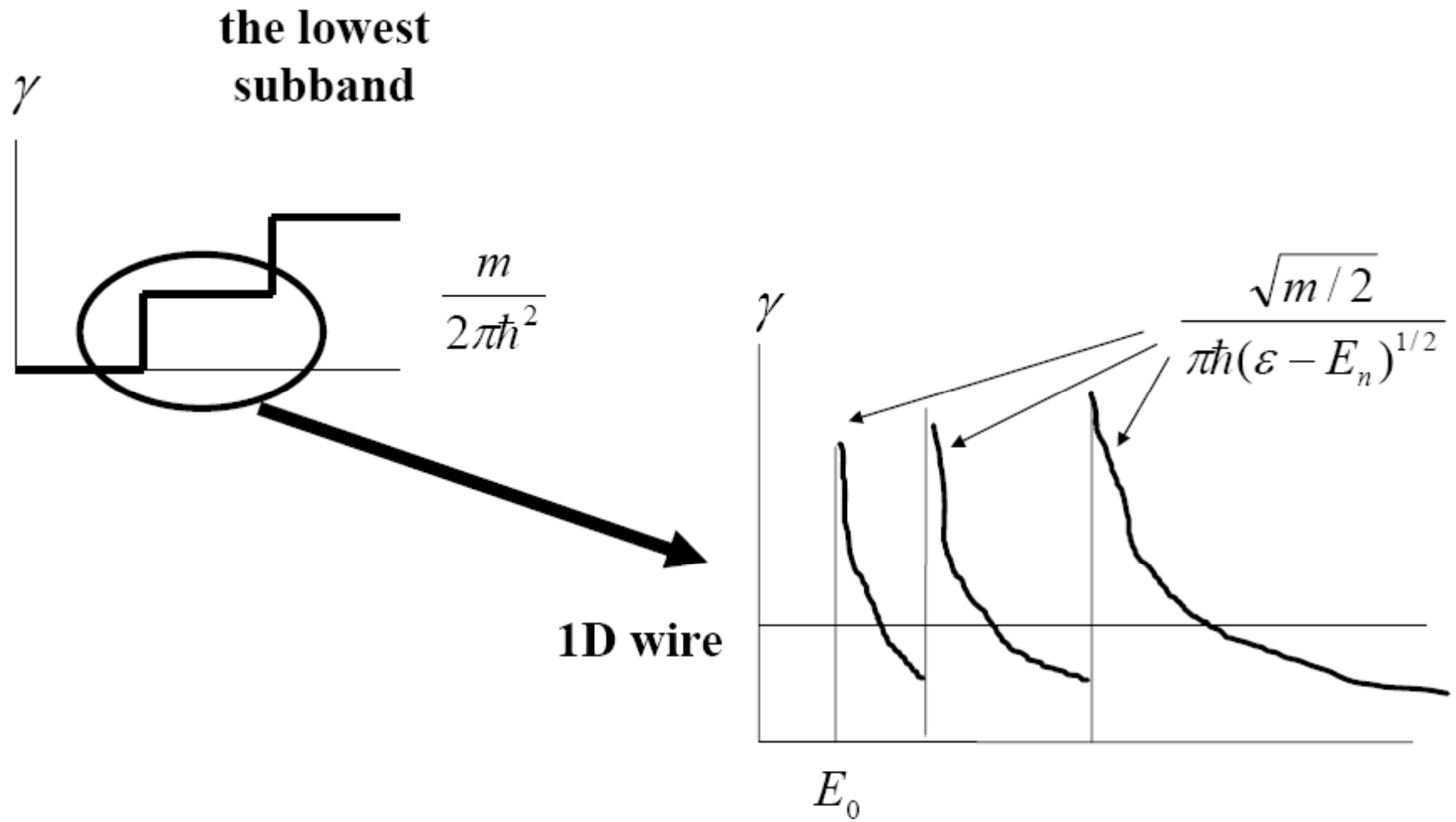
electron beam lithography (0.1-
1micron)



Making quasi-one-dimensional wires using lithographically processed metallic gates

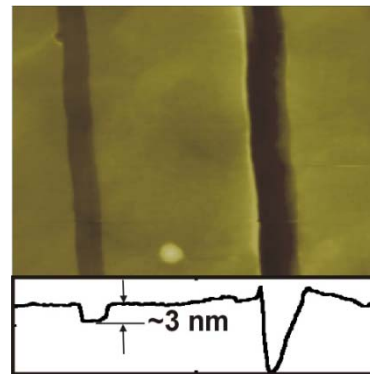
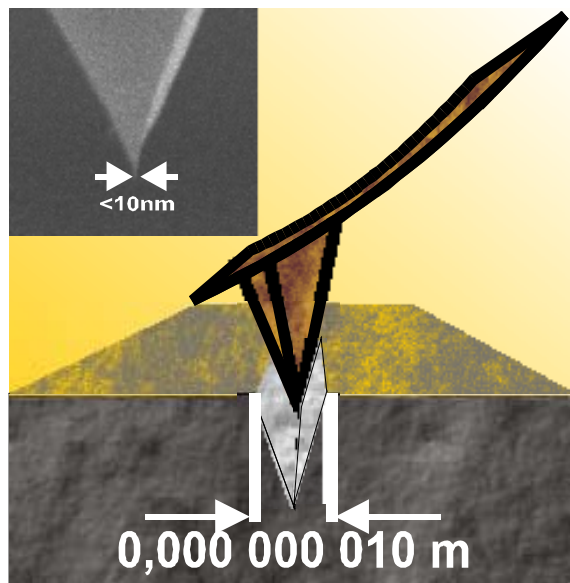


Density of states, γ

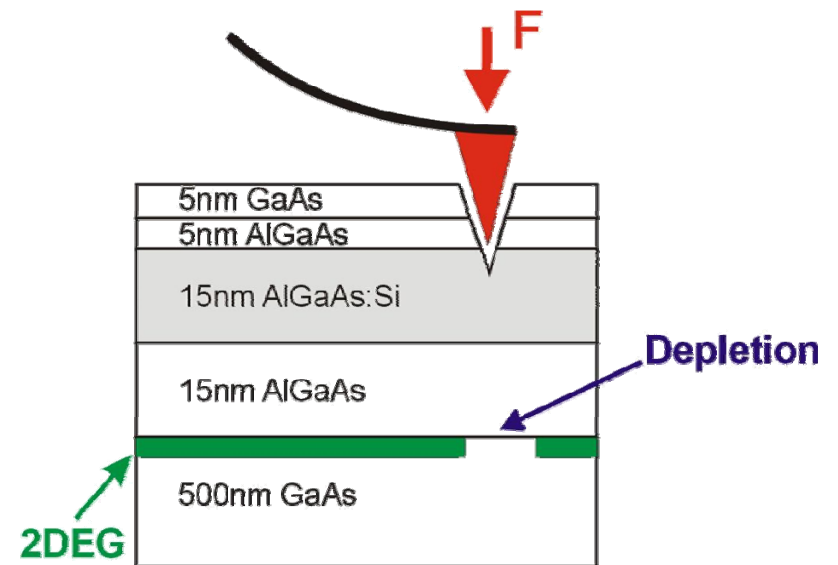


Surface Modification (direct writing) with an AFM (10-100nm)

nanomachining

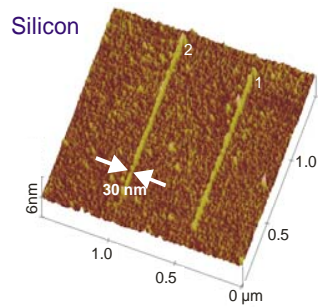
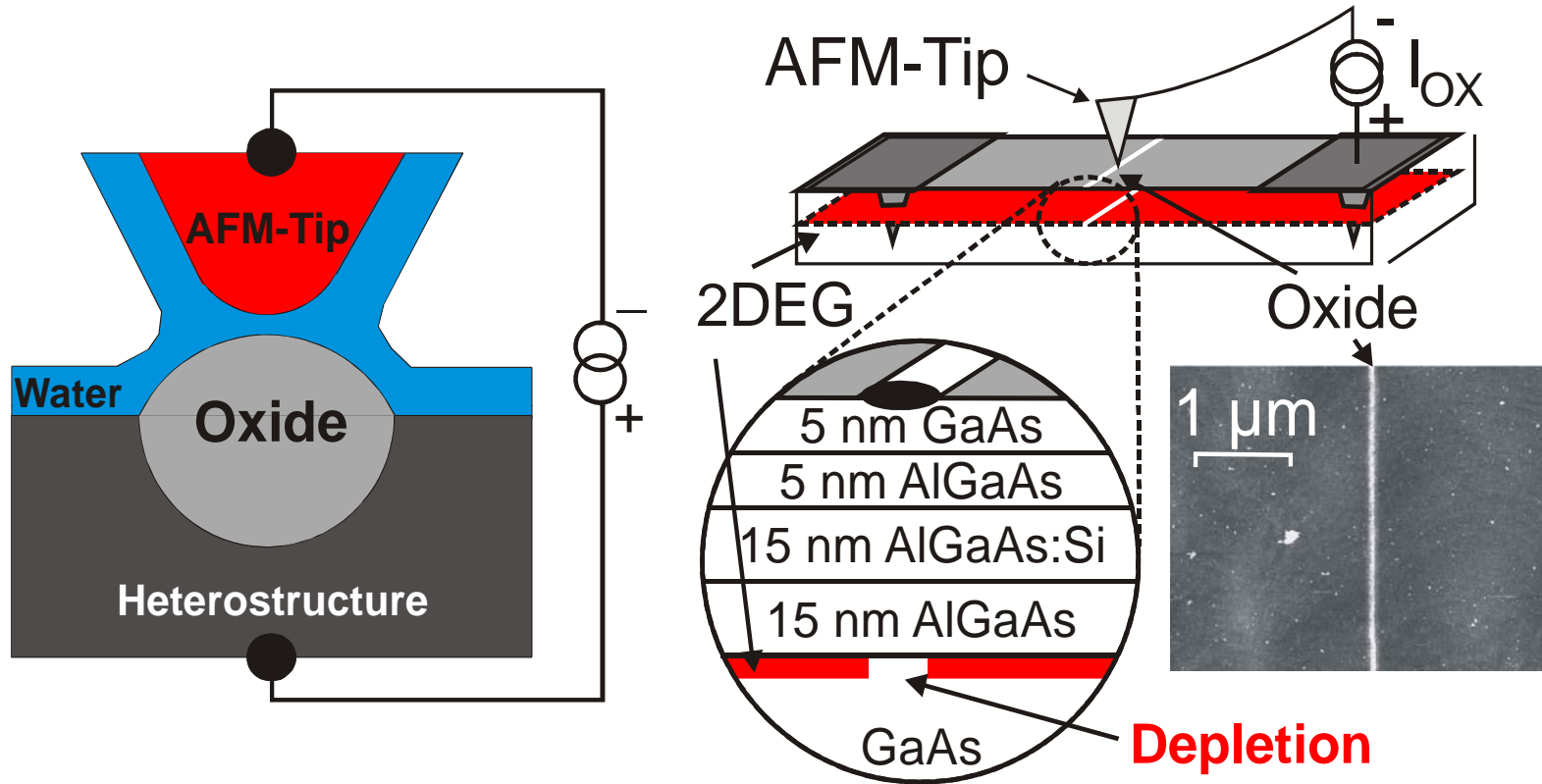


application:
GaAs/AlGaAs-heterostructure



Haug et al, Appl. Phys. Lett. 75, 1107 (1999)

Local Oxidation (10-100nm)



Ishii, Matsumoto (1995), Held et al. (1998)